

### DMTH10H2M5STLWQ

#### 100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI1012-8

#### **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I <sub>D</sub> T <sub>C</sub> = +25°С	
100V	2.5mΩ @ V <sub>GS</sub> = 10V	248A	

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Motor Control
- DC-DC Converters
- Power Management

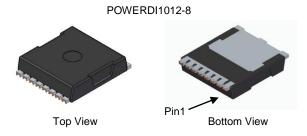
#### Features

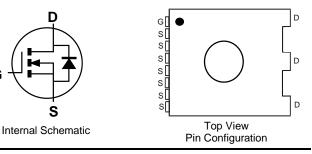
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON) Minimizes On State Losses
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH10H2M5STLWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

- Case: POWERDI<sup>®</sup>1012-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.388 grams (Approximate)





### Ordering Information (Note 4)

Part Number		Case	Packaging		
DMTH10H2M5STLWQ-13		POWERDI1012-8	1500/Tape & Reel		
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.					

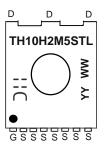
EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

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3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



)|| = Manufacturer's Marking TH10H2M5STL = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)

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# Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	Vdss	100	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		ID	248 175	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	992	А	
Maximum Continuous Body Diode Forward Current (Note 6)	ls	248	А	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	lsм	992	А	
Avalanche Current, L = 0.3mH	las	68	А	
Avalanche Energy, L = 0.3mH	Eas	701	mJ	

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	5.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	26	°C/W	
Total Power Dissipation (Note 6) T <sub>C</sub> = +25°C		PD	230.8	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	0.65	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	2	—	4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	1.68	2.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A	
Diode Forward Voltage	Vsd	_	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 30A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	8450	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	—	2430	_	pF		
Reverse Transfer Capacitance	Crss	—	17.7	—			
Gate Resistance	Rg	—	1.0	—	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	QG	—	124.4	—			
Gate-Source Charge	Q <sub>GS</sub>	_	34	_	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 30A, V <sub>GS</sub> = 10V	
Gate-Drain Charge	QGD	—	28.3	—			
Turn-On Delay Time	tD(ON)	_	32.7	_			
Turn-On Rise Time	tR	_	47	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_D = 30A, R_G = 4.7\Omega$	
Turn-Off Delay Time	tD(OFF)	_	91.3	_	ns		
Turn-Off Fall Time	tF	_	53.9	_			
Reverse Recovery Time	t <sub>RR</sub>	_	87.6	_	ns	I= 254 di/dt 1004/u-	
Reverse Recovery Charge	Q <sub>RR</sub>	_	251.8		nC	IF = 25A, di/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

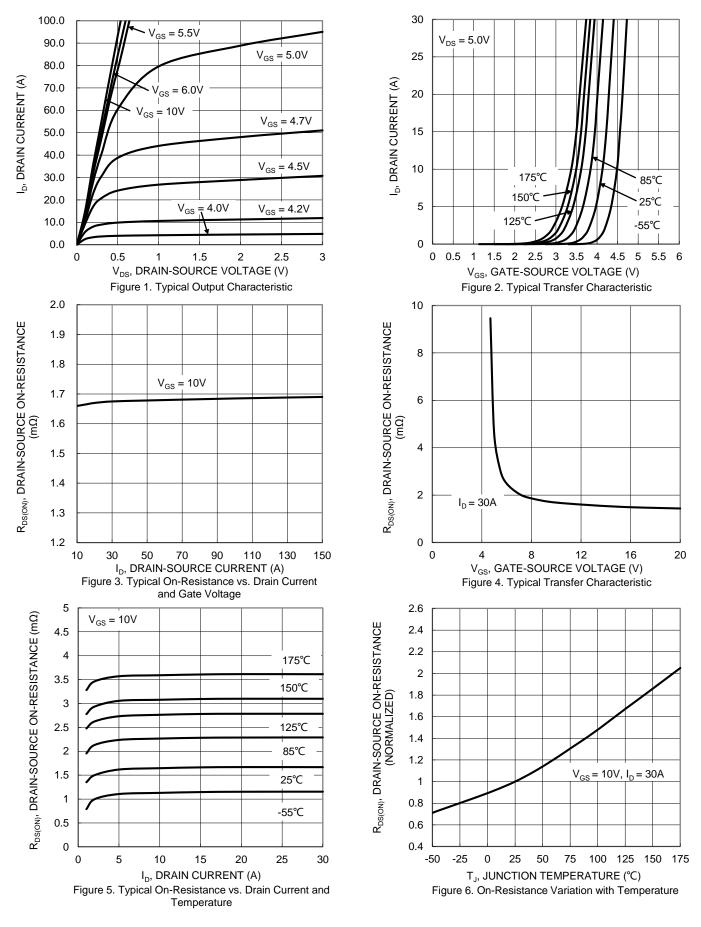
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

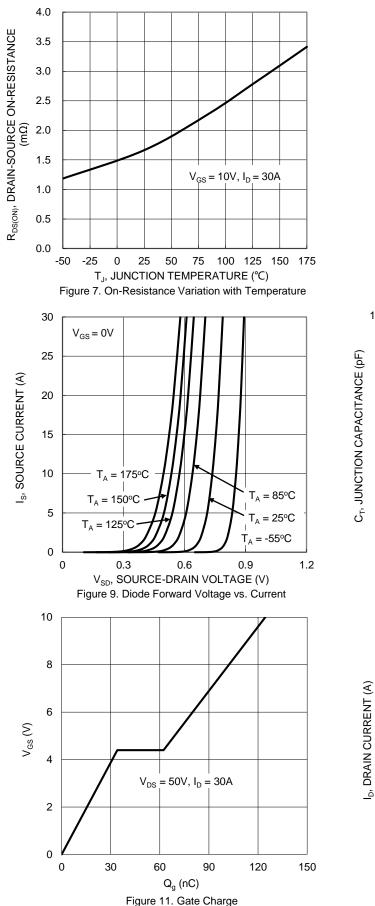


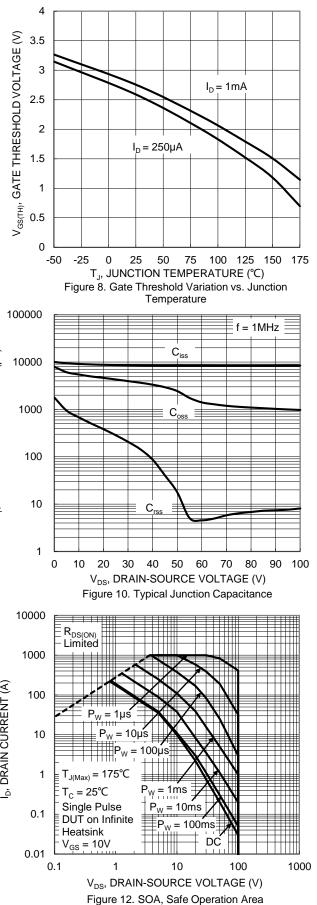
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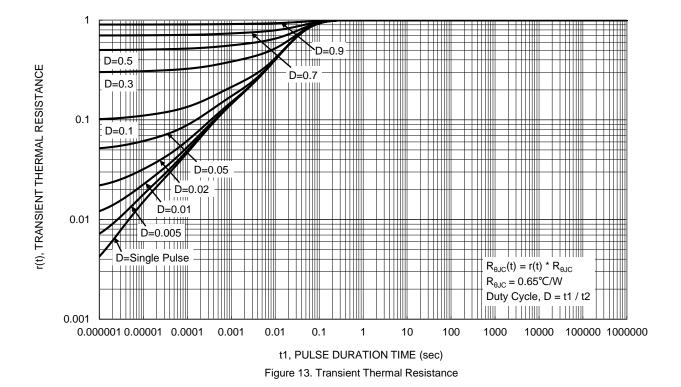






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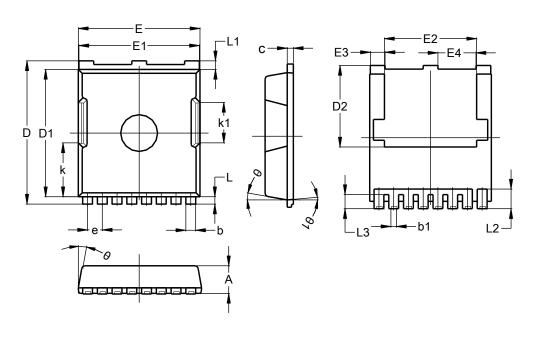






### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



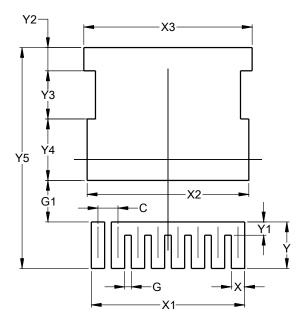
POWERDI1012-8					
Dim	Min Max T		Тур		
Α	2.20	2.40	2.30		
b	0.70	0.90	0.80		
b1	0.42	0.50	0.45		
С	0.40	0.60	0.50		
D	11.48	11.88	11.68		
D1	10.23	10.53	10.38		
D2	6.45	6.45 6.85 6.65			
E	9.70 10.10 9.9		9.90		
E1	9.70	9.90	9.80		
E2	7.00	8.00	7.50		
E3	1.10	1.30	1.20		
E4	3.00	3.20	3.10		
е	1.20 BSC				
k	4	4.39 REF	-		
k1		3.30 REF	-		
L	0.50	0.70	0.60		
L1	0.50	0.90	0.70		
L2	1.40	1.80	1.60		
L3	1.00	1.30	1.15		
θ	0°	15°	10º		
θ1	0°	10º	5°		
All Dimensions in mm					

#### POWERDI1012-8

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### POWERDI1012-8



Dimensions	Value (in mm)			
С	1.200			
G	0.400			
G1	2.500			
Х	0.800			
X1	9.200			
X2	9.700			
Х3	10.100			
Y	2.800			
Y1	0.800			
Y2	1.400			
Y3	2.900			
Y4	3.700			
Y5	13.300			



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